



VEC2415 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Composite type facilitating high-density mounting
- 4V drive
- Mounting high 0.75mm
- Protection diode in

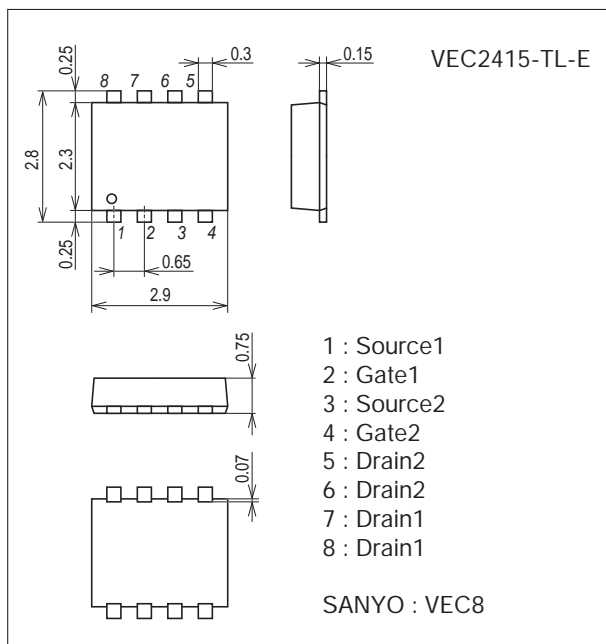
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		3	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	12	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	0.9	W
Total Dissipation	P _T	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.0	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions

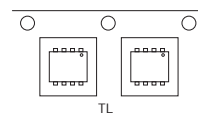
unit : mm (typ)
7012-002



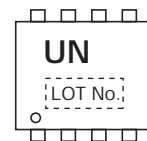
Product & Package Information

- Package : VEC8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

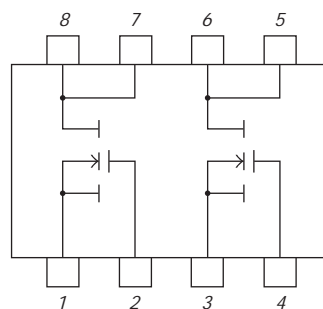
Packing Type : TL



Marking



Electrical Connection

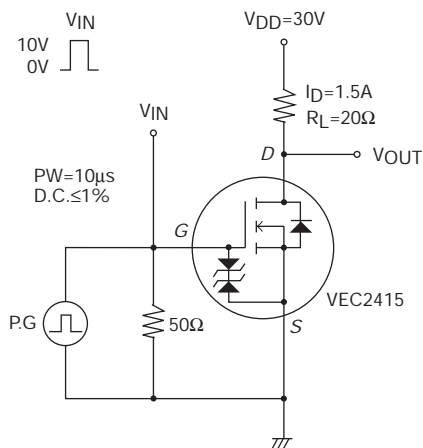


VEC2415

Electrical Characteristics at Ta=25°C

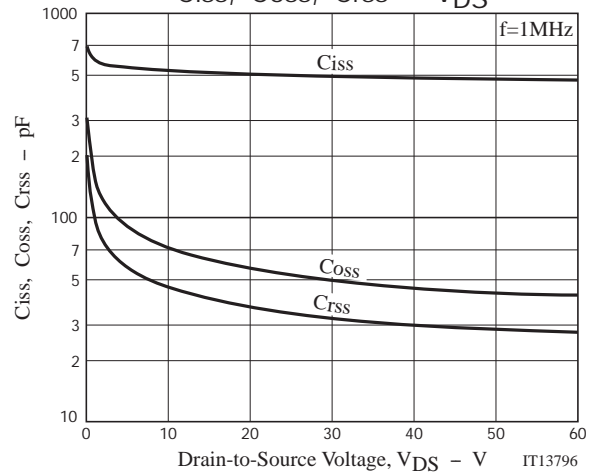
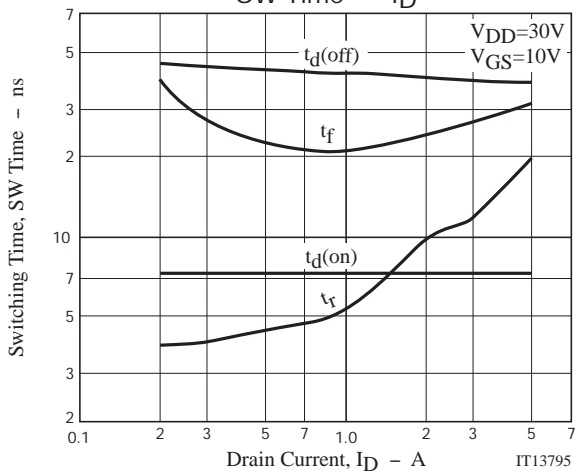
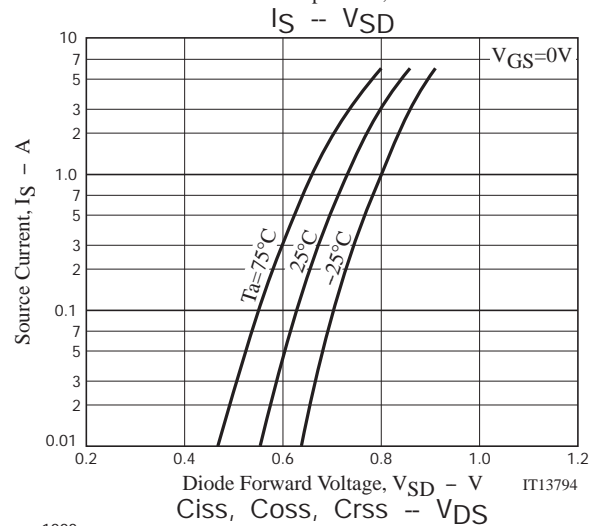
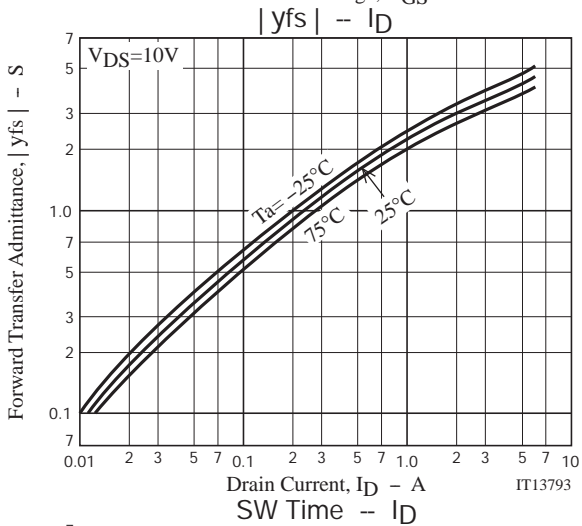
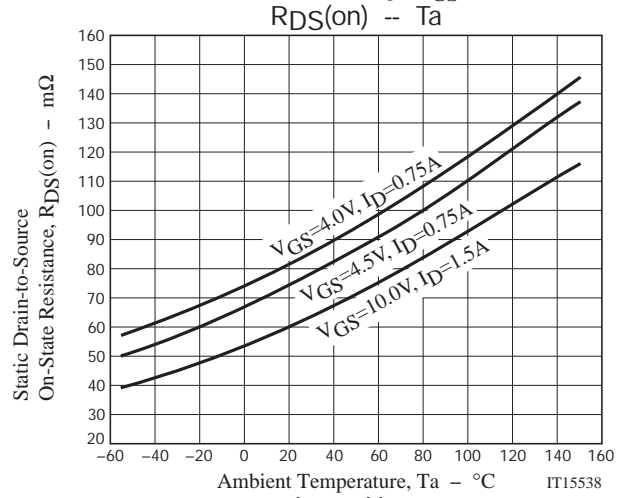
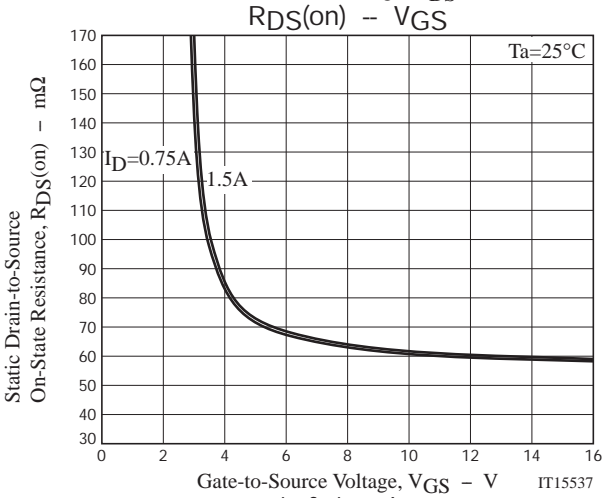
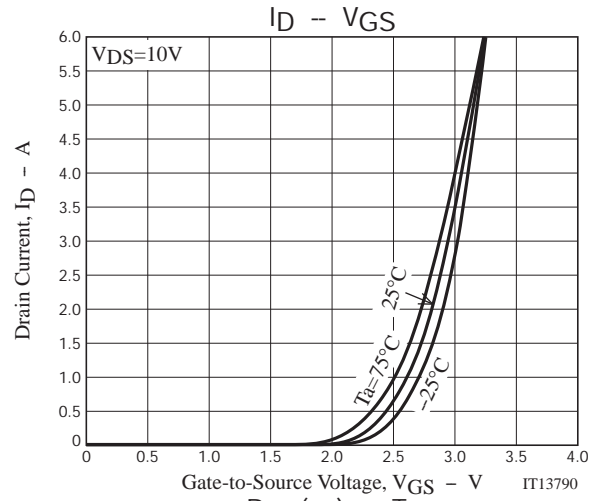
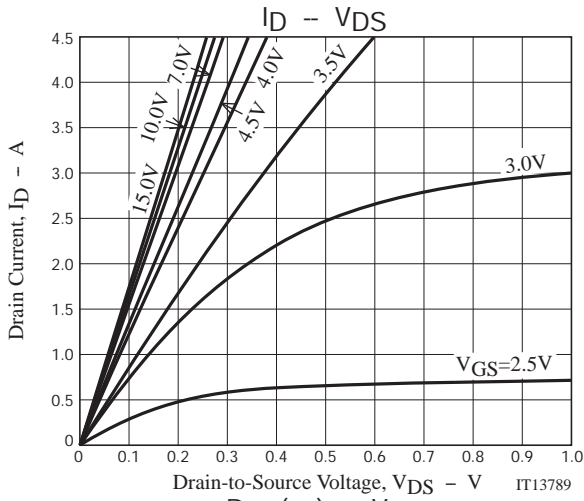
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	60			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=1.5A$		2.6		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=1.5A, V_{GS}=10V$		62	80	$m\Omega$
	$R_{DS(on)2}$	$I_D=0.75A, V_{GS}=4.5V$		76	106	$m\Omega$
	$R_{DS(on)3}$	$I_D=0.75A, V_{GS}=4V$		83	116	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V, f=1MHz$		505		pF
Output Capacitance	C_{oss}			57		pF
Reverse Transfer Capacitance	C_{rss}			37		pF
Turn-ON Delay Time	$t_d(on)$			7.3		ns
Rise Time	t_r	See specified Test Circuit.		7.5		ns
Turn-OFF Delay Time	$t_d(off)$			41		ns
Fall Time	t_f			22		ns
Total Gate Charge	Q_g	$V_{DS}=30V, V_{GS}=10V, I_D=3A$		10		nC
Gate-to-Source Charge	Q_{gs}			1.6		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			2.1		nC
Diode Forward Voltage	V_{SD}	$I_S=3A, V_{GS}=0V$		0.81	1.2	V

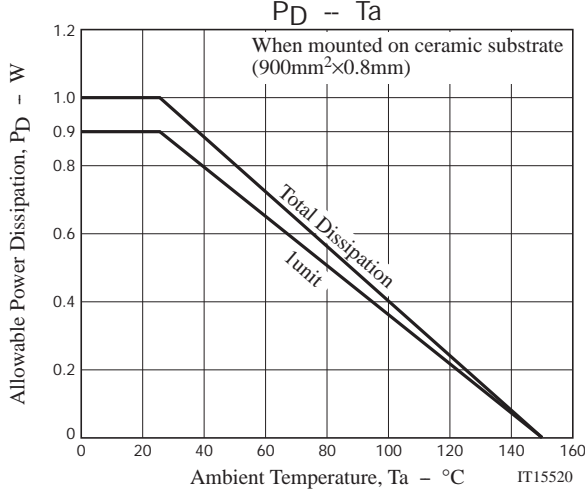
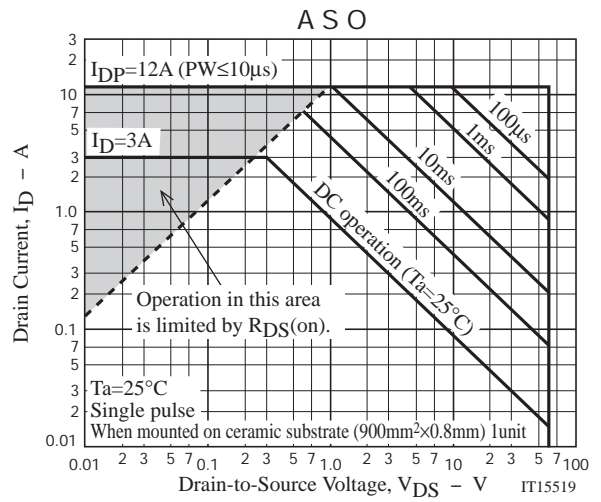
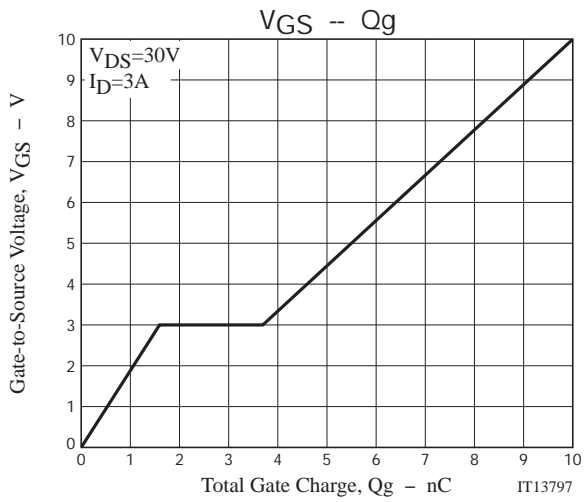
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
VEC2415-TL-E	VEC8	3,000pcs./reel	Pb Free





VEC2415

Taping Specification

VEC2415-TL-E

1. Packing Format

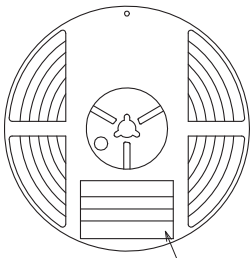
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
VEC8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit:mm)

Outer box label

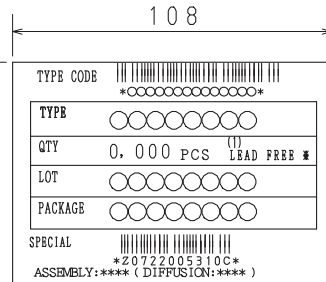
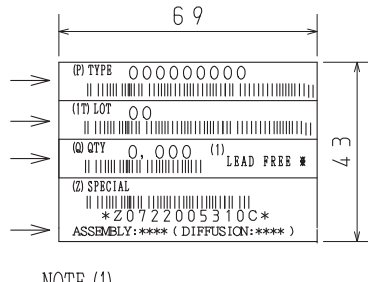
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Reel label

Type No.
LOT No.
Quantity
Origin



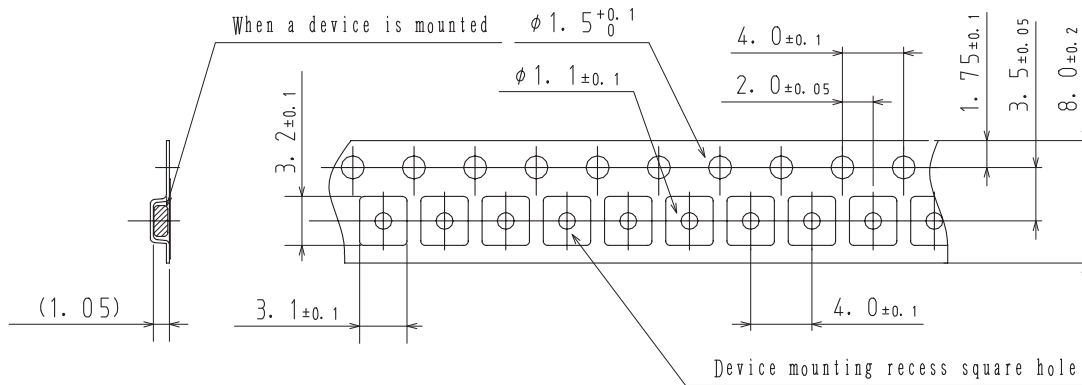
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

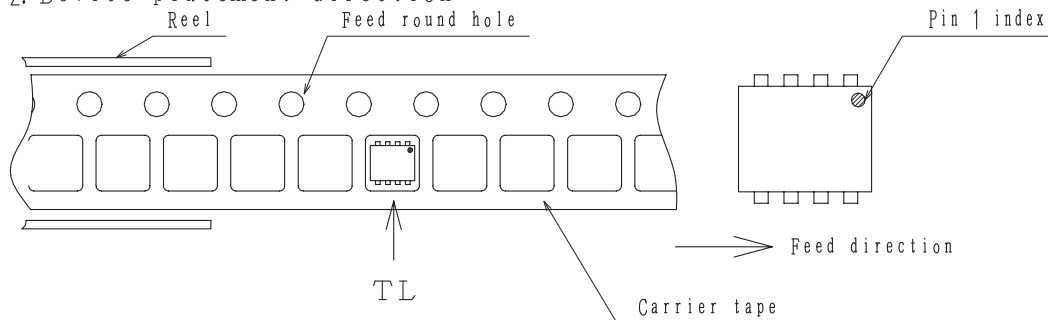
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



Those with open electrode terminal on the feed hole side.....TL

Note on usage : Since the VEC2415 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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